

Various consequences of disorder on strongly correlated systems

D.D. Sarma

Solid State and Structural Chemistry Unit

Indian Institute of Science

Bangalore

sarma@sscu.iisc.ernet.in

<http://sscu.iisc.ernet.in/DDSarma/>

- Sugata Ray
- Dinesh Topwal
- Manju Unnikrishnan
- Prabuddha Sanyal
- Subhra Sengupta
- Priya Mahadevan
- Tanusri Saha-Dasgupta
- H.R. Krishnamurthy
- Chandan Dasgupta
- E. V. Sampathkumaran
- A. Fujimori
- Y. Tokura
- C. Meneghini
- C. Segre
- D. Matsumura and T. Ohta

Department of Science and Technology, Government of India

$\text{Sr}_2\text{FeMoO}_6$ - a compound with many faces

In general $A_2BB'O_6$ 

Ordered

Double

Perovskite

Is it $ABO_3 + AB'O_3$?

$\text{Sr}_2\text{FeMoO}_6$:

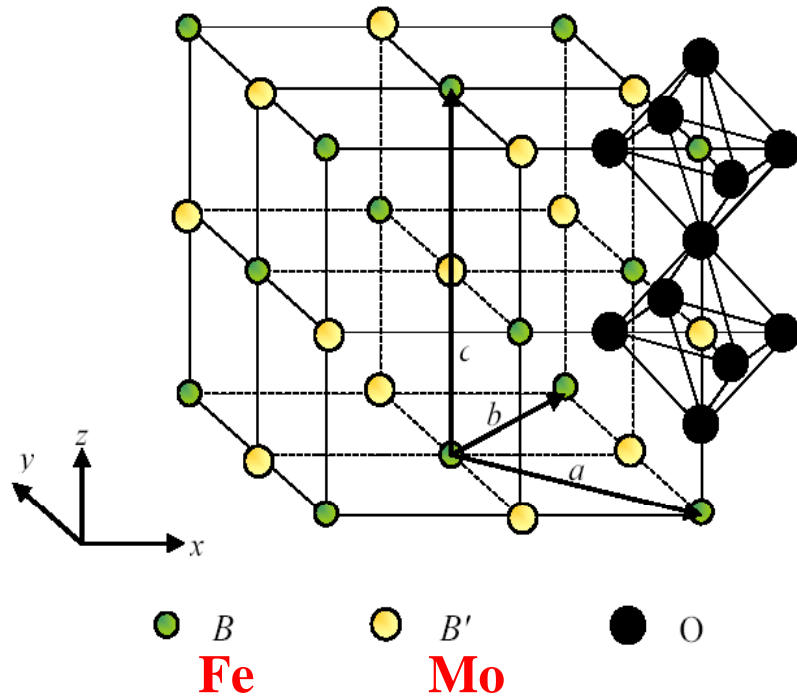
$\text{Sr}_2\text{Fe}_{1-x}\text{Mo}_{1+x}\text{O}_6$
($\text{SrFeO}_3/\text{SrMoO}_3$),

$\text{Sr}_2\text{FeMo}_{1-x}\text{W}_x\text{O}_6$
($\text{Sr}_2\text{FeMoO}_6/\text{Sr}_2\text{FeWO}_6$)

$\text{Mn}_x\text{Ga}_{1-x}\text{As}$ and $\text{Tl}_2\text{Mn}_2\text{O}_7$

Some typical publications in this field from our group

- **Phys. Rev. Lett. (in press 2009).**
- **Phys. Rev. Lett. 100, 186402 (2008).**
- **Phys. Rev. Lett. 98, 246401 (2007).**
- **Phys. Rev. Lett. 98, 157205 (2007).**
- **Phys. Rev. Lett. 96, 087205 (2006)**
- **Phys. Rev. Lett. 95, 117201 (2005).**
- **Nano Lett. 2, 605 (2002).**
- **Phys. Rev. Lett. 87, 097204 (2001).**
- **Phys. Rev. Lett. 85, 2549 (2000).**
- **Solid State Comm. 114, 465 (2000).**

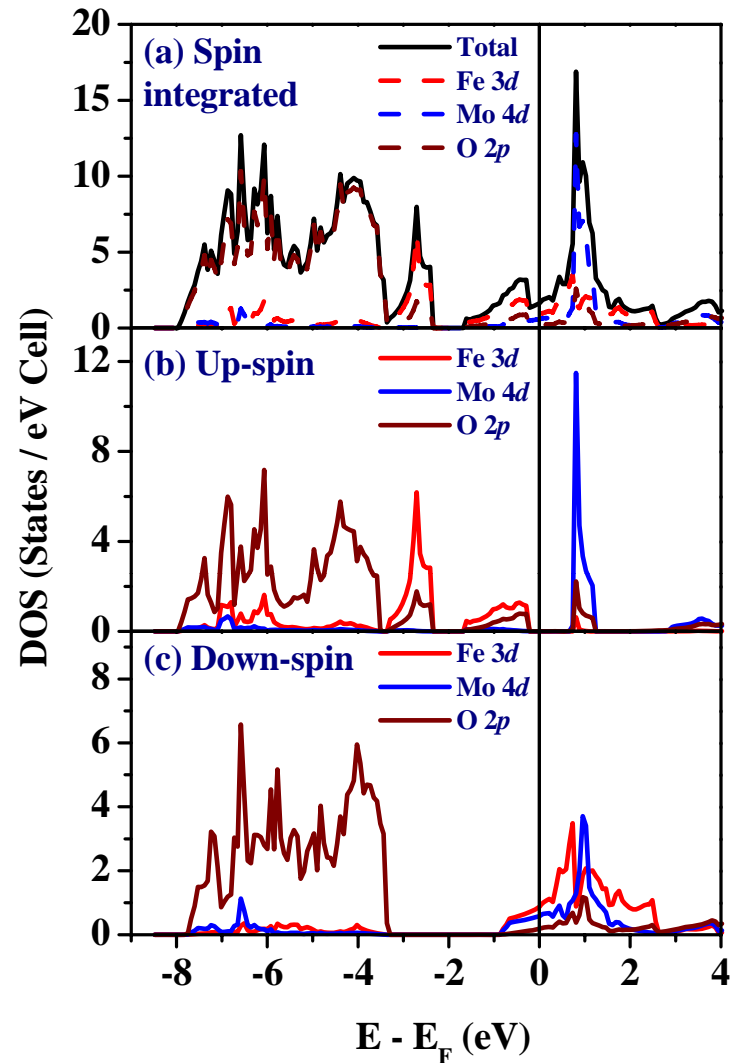


Crystal structure of **ordered**
double perovskite: $A_2BB'O_6$
↙ ↘ ↙ ↘ ↙ ↘ ↙ ↘
Sr Fe Mo O

D.D.Sarma, *Current Opinion in Solid State and Materials Science* (2001)

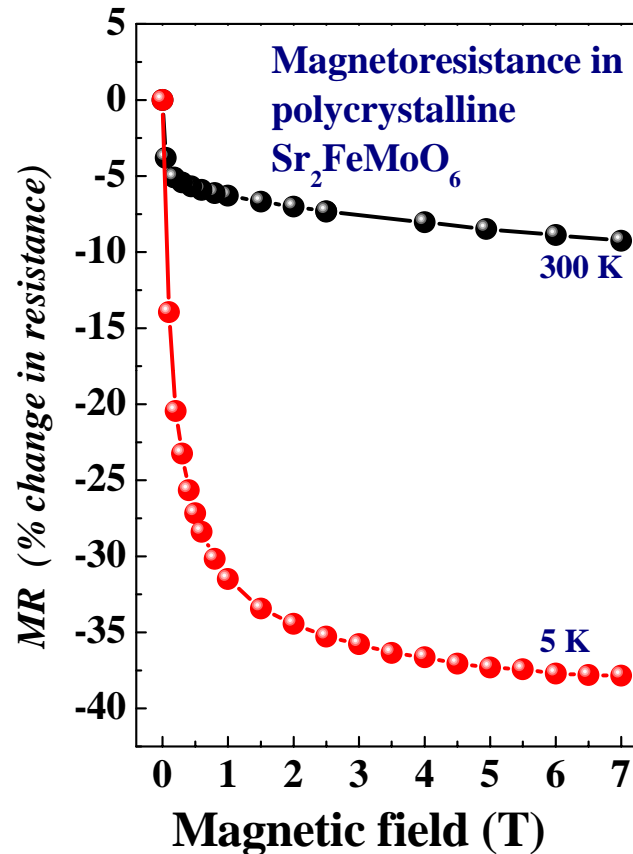
and

Phys. Rev. Lett. 85, 2549 (2000).



LMTO band structure results of
 Sr_2FeMoO_6

Magnetoresistance in polycrystalline $\text{Sr}_2\text{FeMoO}_6$



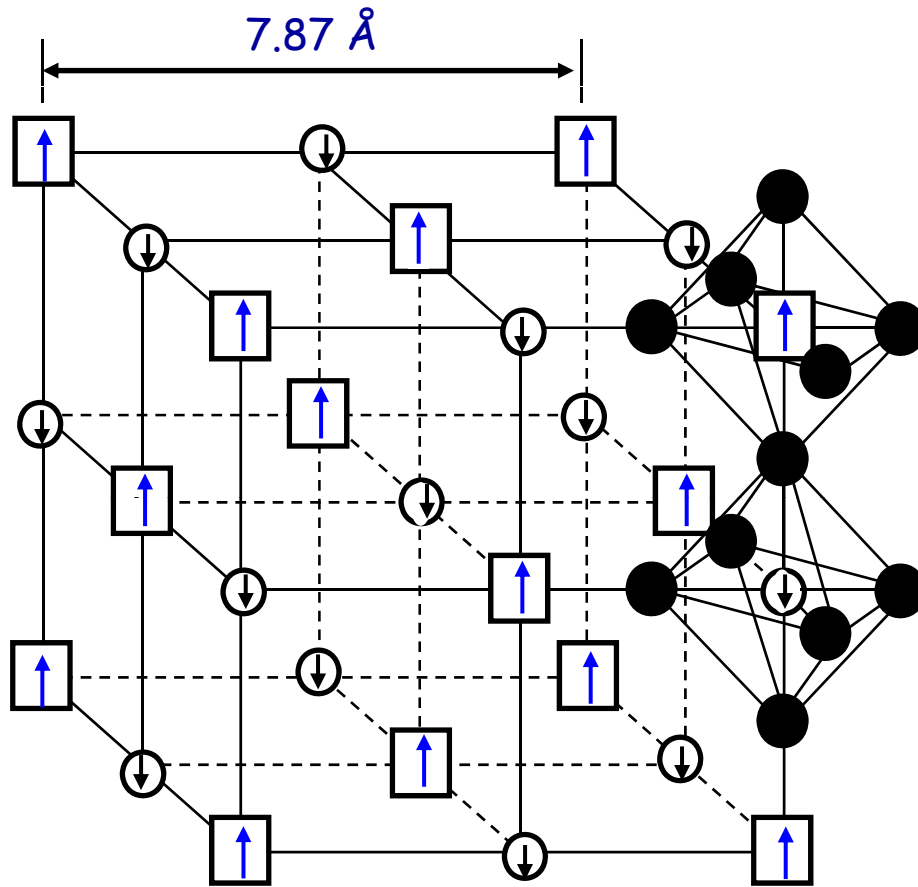
Sarma et al., Solid State Comm. 114, 465 (2000).

Several advantages:

- Large MR at higher T and lower H.
- High ferromagnetic T_c .
- Half-metallic ferromagnet (100% spin polarization of charge carriers).
- Simple crystal structure. Possibly, no serious complication arising from J-T type distortions.

Therefore, attractive both in terms of theoretical investigations and possible technological applications.

On the basis of the structural data, however, ferromagnetism appears to be a rather unexpected ground state for this system.



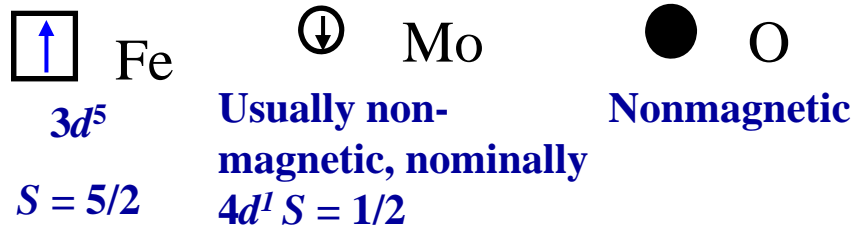
$$T_C = 420 \text{ K}$$

Weak AF interaction between Fe ions, governed by super-exchange, is expected and also found in Sr_2FeWO_6

What is the origin of the strong ferromagnetic interaction between Fe ions in this compound, implicit in such an unusually high T_C ?

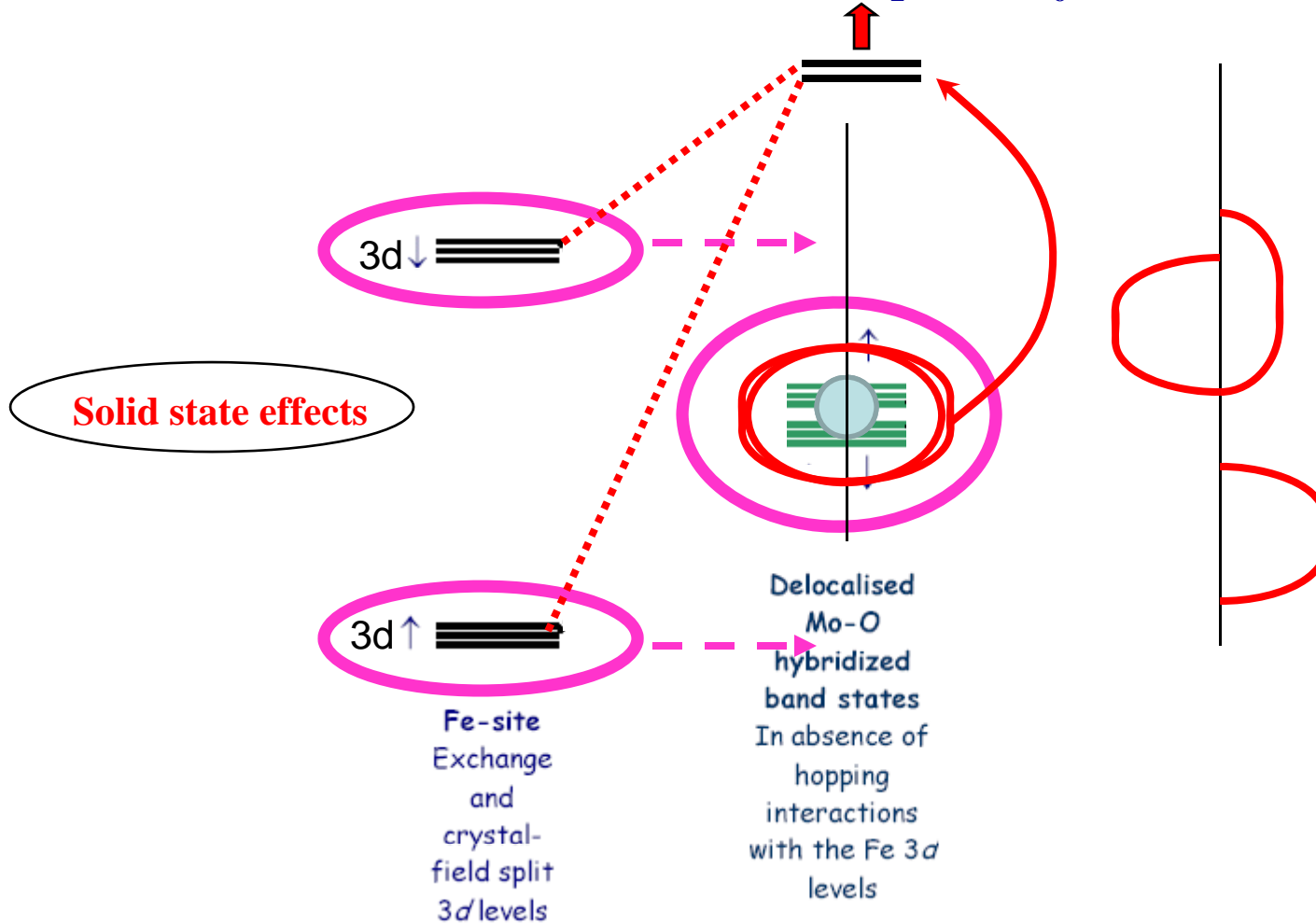
Superexchange between Fe up- and Mo down-spins?

Or double-exchange?



Must be a different mechanism from the manganites that polarises the delocalised, nominally Mo derived, conduction electrons.

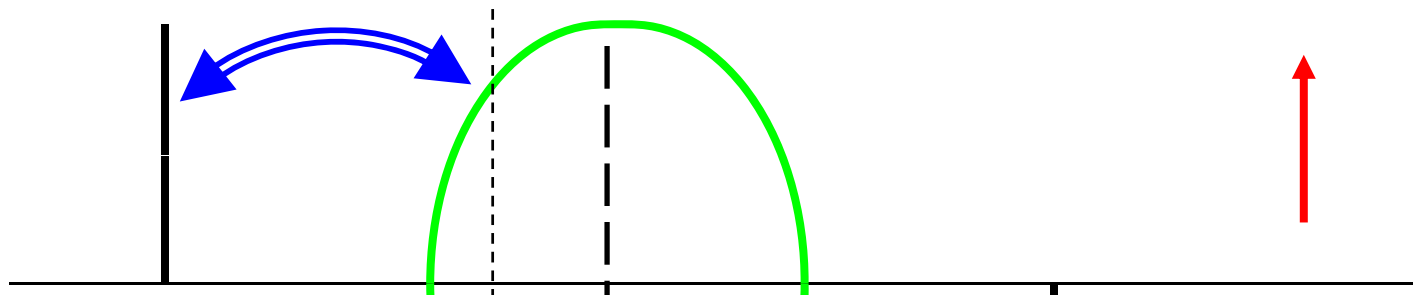
Origin of the robust ferromagnetism in double perovskite, $\text{Sr}_2\text{FeMoO}_6$



Intra-atomic, $I_{\text{eff}} \sim 1-1.5 \text{ eV}$, Inter-atomic, $J \sim 18 \text{ meV}$

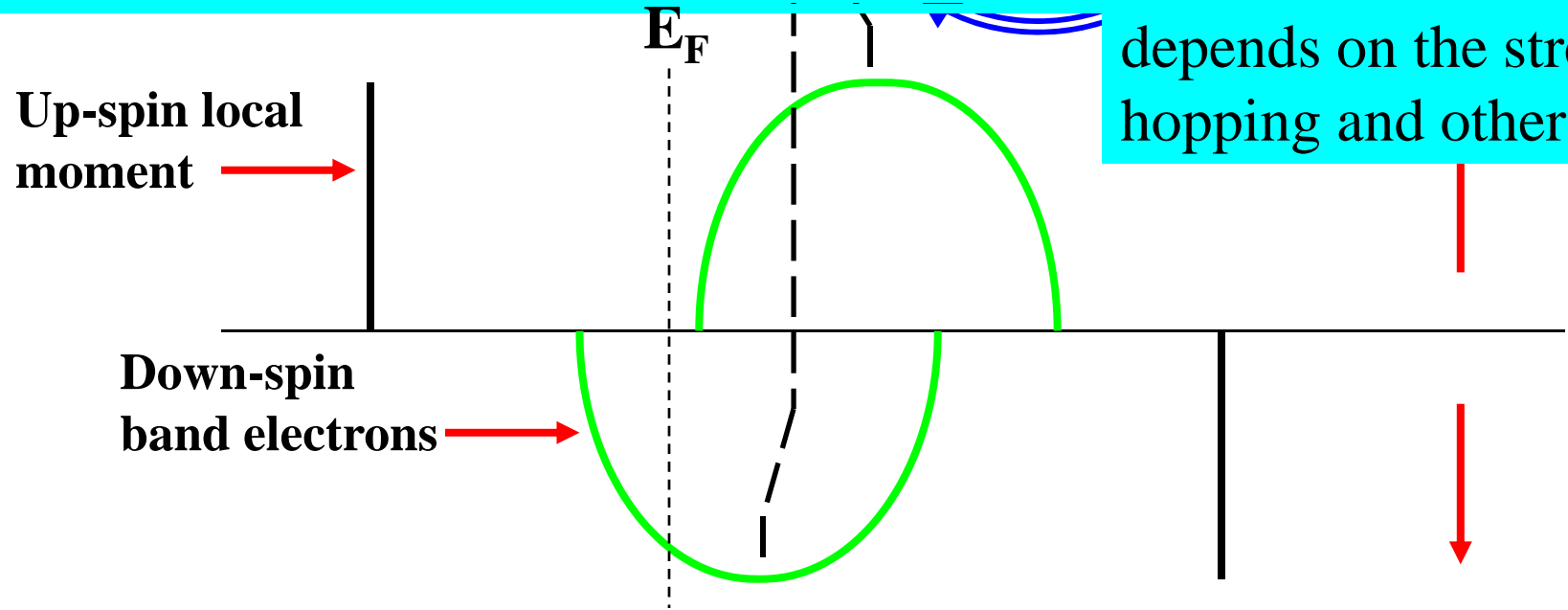
Why Sr_2FeWO_6 is an antiferromagnet?

Sarma et al., PRL 85, 2549 (2000).



Hopping induced antiferromagnetic coupling of itinerant and localized spins \Rightarrow Ferromagnetic coupling of the localized moments.

Half-metallic or not depends on the strength of hopping and other details.

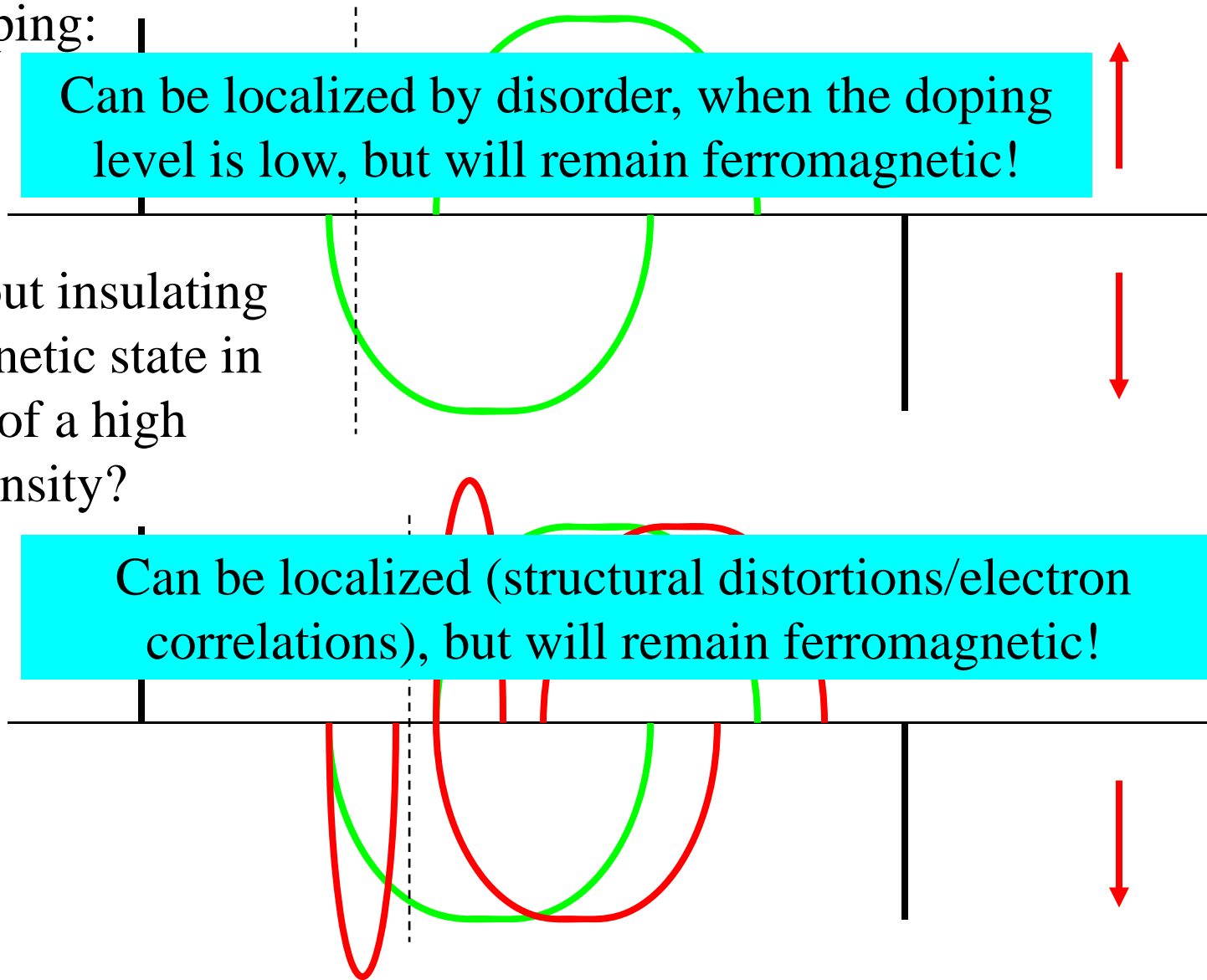


Low doping:

Can be localized by disorder, when the doping level is low, but will remain ferromagnetic!

What about insulating ferromagnetic state in presence of a high carrier density?

Can be localized (structural distortions/electron correlations), but will remain ferromagnetic!



Magnetism in

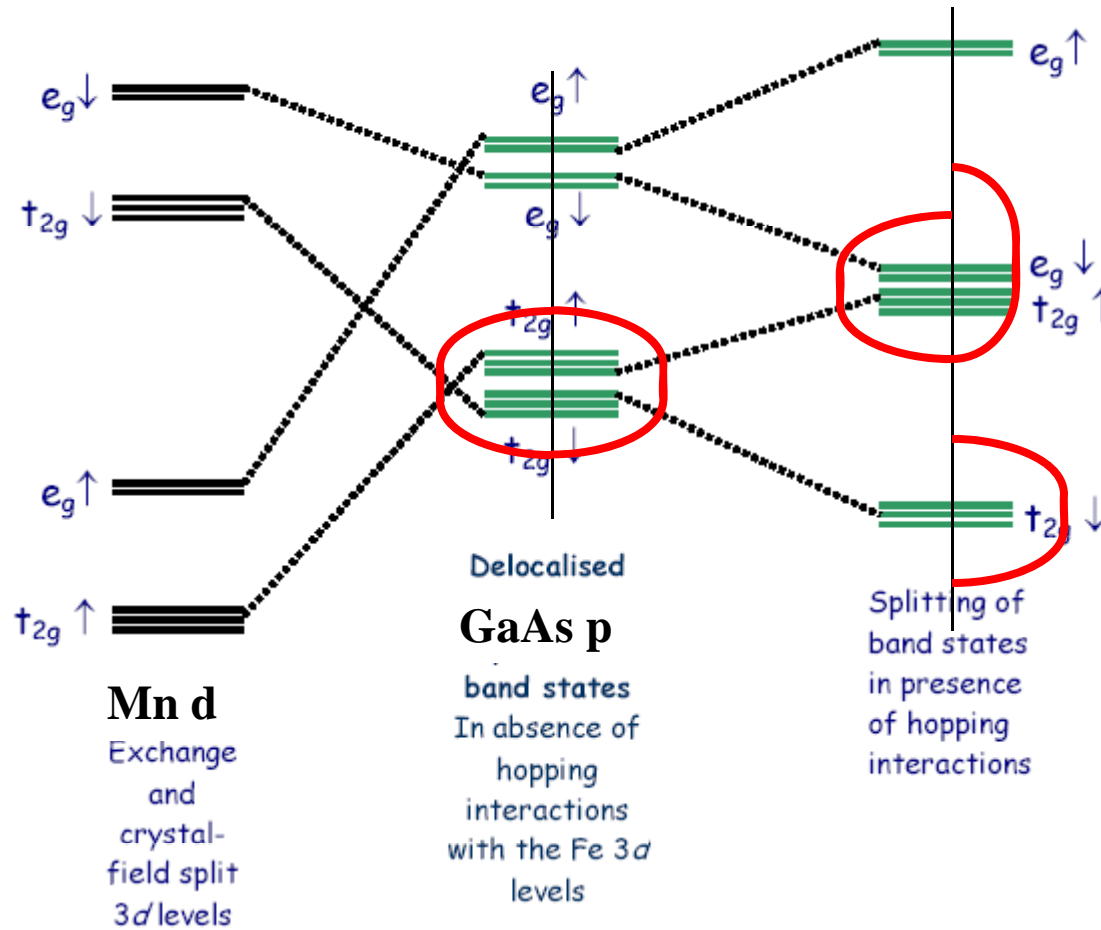
$\text{Mn}_x\text{Ga}_{1-x}\text{As}$:

Mahadevan, Zunger and Sarma,
Phys. Rev. Lett. 93, 177201 (2004).

$\text{Tl}_2\text{Mn}_2\text{O}_7$:

Saha-Dasgupta, De Raychaudhury and Sarma,
Phys. Rev. Lett. 96, 087205 (2006).

Origin of the ferromagnetism in Mn-doped GaAs



Ferromagnetism in Mn-doped GaAs

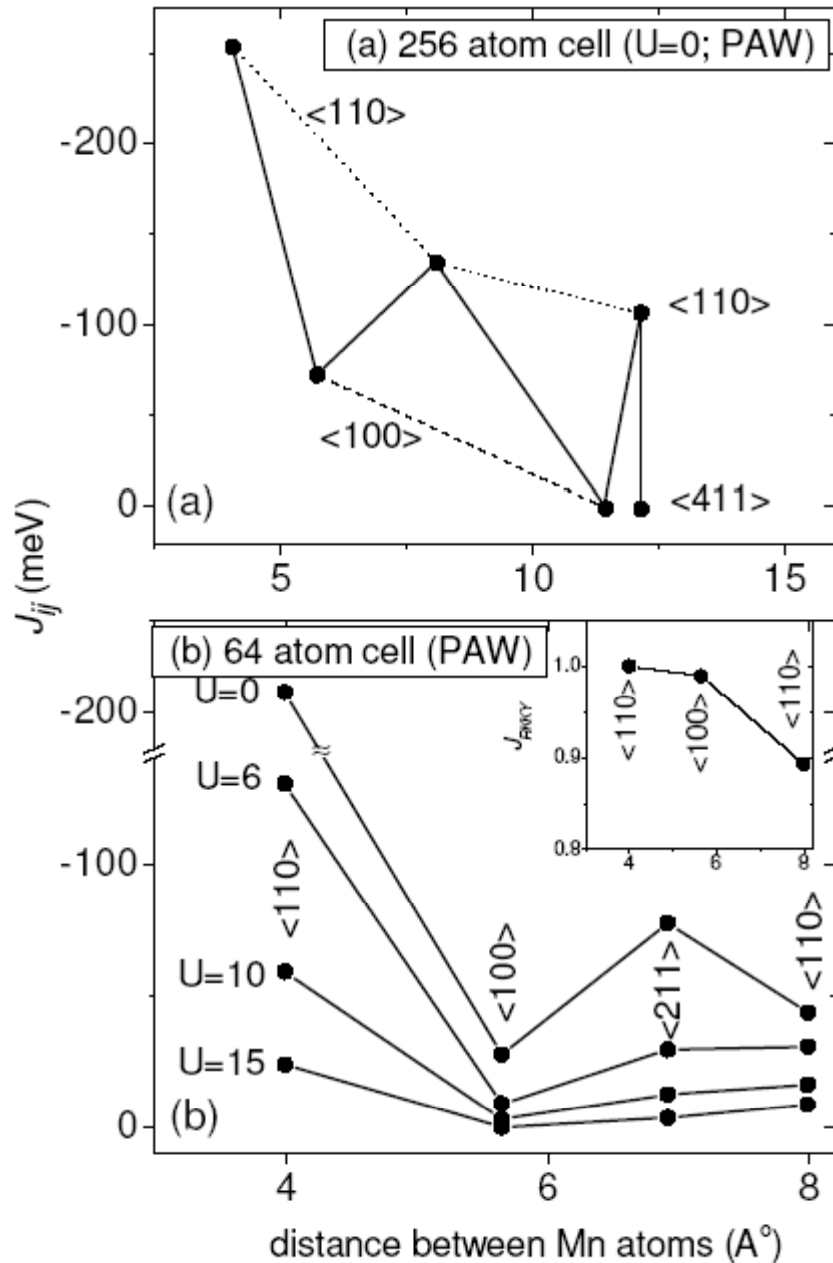


FIG. 4: The distance/orientation dependence of J_{ij} for Mn pairs in (a) 256, (b) 64 atom GaAs cell using PAW potentials. The expected dependence of J_{RKKY} for a hole in GaAs is given in the insert.

Mahadevan, Zunger and Sarma, Phys. Rev. Lett. 93, 177201 (2004).

LETTERS

Atom-by-atom substitution of Mn in GaAs and visualization of their hole-mediated interactions

Dale Kitchen^{1,2}, Anthony Richardella^{1,2}, Jian-Ming Tang³, Michael E. Flatté³ & Ali Yazdani¹

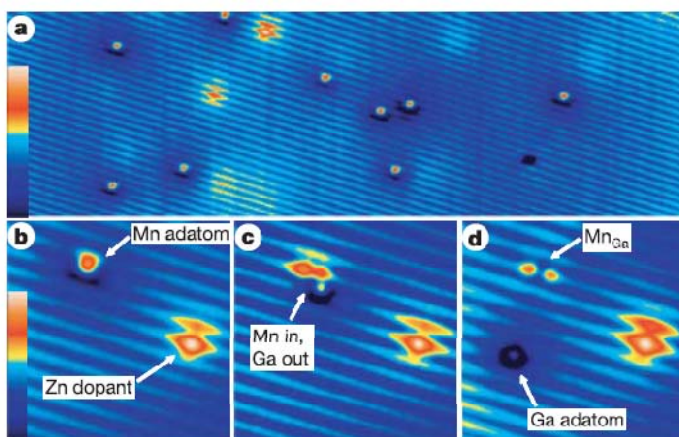


Figure 1 | Single-atom substitution of one Mn for one Ga atom. **a**, Large topograph of the occupied states ($500 \times 150 \text{ \AA}^2$; -2 V ; $0-1.5 \text{ \AA}$) showing many Mn adsorbates and a few subsurface Zn dopants. **b-d**, High-resolution topographs (75 \AA^2 ; -2 V ; $0-1.3 \text{ \AA}$). **b**, Mn adsorbate and a Zn acceptor visible on the As sublattice. **c**, STM-assisted incorporation of the Mn into a Ga site forcing the substituted Ga atom to the surface. **d**, Tip-pulses move the Ga adatom from the incorporation site, isolating a Mn acceptor (Mn_{Ga}).

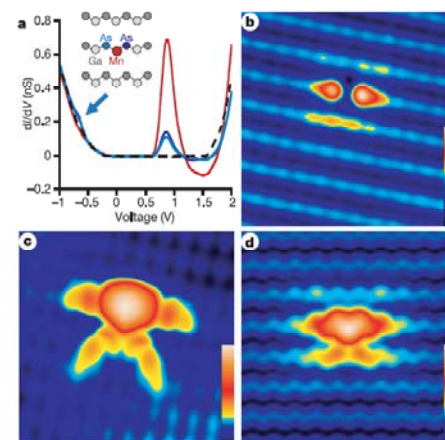


Figure 2 | High-resolution measurements of a single Mn acceptor (Mn_{Ga}). **a**, Spatially resolved dI/dV measurements near an Mn acceptor. The As neighbours show enhancements deep in the valence band, highlighted by the blue arrow. The large in-gap resonance over the Mn is its acceptor level. **b**, 40 \AA^2 topograph of the occupied states (-1.5 V ; $0-0.4 \text{ \AA}$) showing enhancements concentrated on the neighbouring As. **c**, 40 \AA^2 topograph of the unoccupied states ($+1.55 \text{ V}$; $0-4 \text{ \AA}$) revealing the anisotropic shape of the Mn acceptor. **d**, Tight-binding model of a Mn acceptor in bulk GaAs with the Mn spin oriented in-plane along [001]. The image shows a 40 \AA^2 area of the (110) plane containing the Mn. The log of the integrated LDOS from the Fermi level to 1.55 eV is displayed with a spatial broadening factor of 1.7 \AA . The colours in the scales have been chosen to enhance the view of the Mn influence on GaAs.

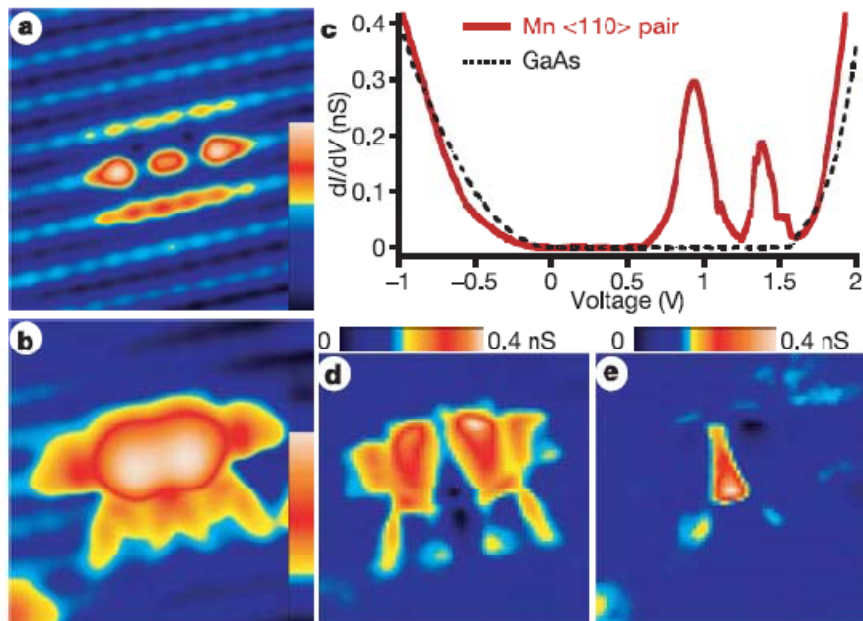


Figure 3 | Mn pair substituted in Ga sites spaced 8 Å apart in a <110> orientation. **a**, 40 Å² topograph of the valence-band states (-1.5 V; 0–0.4 Å). **b**, 40 Å² topograph of the in-gap states showing the bound states of Mn acceptors (+1.1 V; 0–4 Å). **c**, dI/dV measurements near the Mn pair, revealing two resonance levels in the gap. **d**, Differential conductance energy map at +1.35 V displaying the bonding nature of the higher energy resonance. **e**, Energy map at +0.91 V displaying the anti-bonding nature of the lower energy peak.

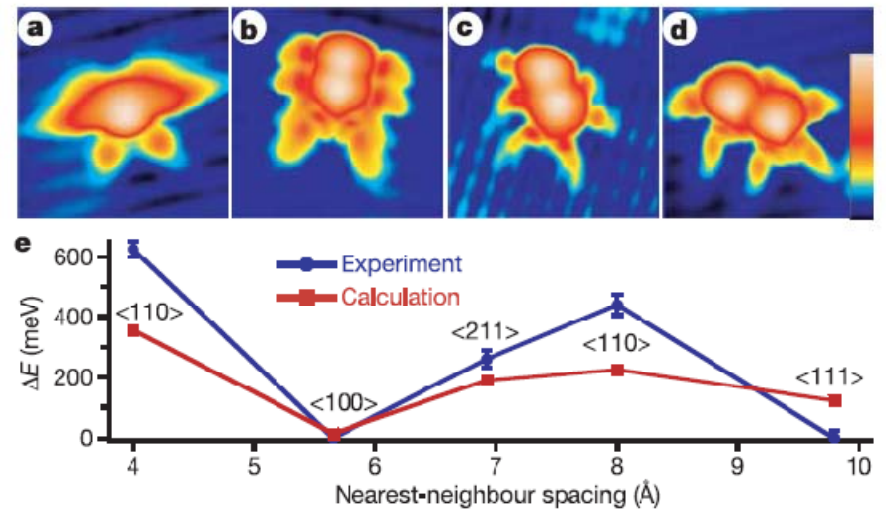
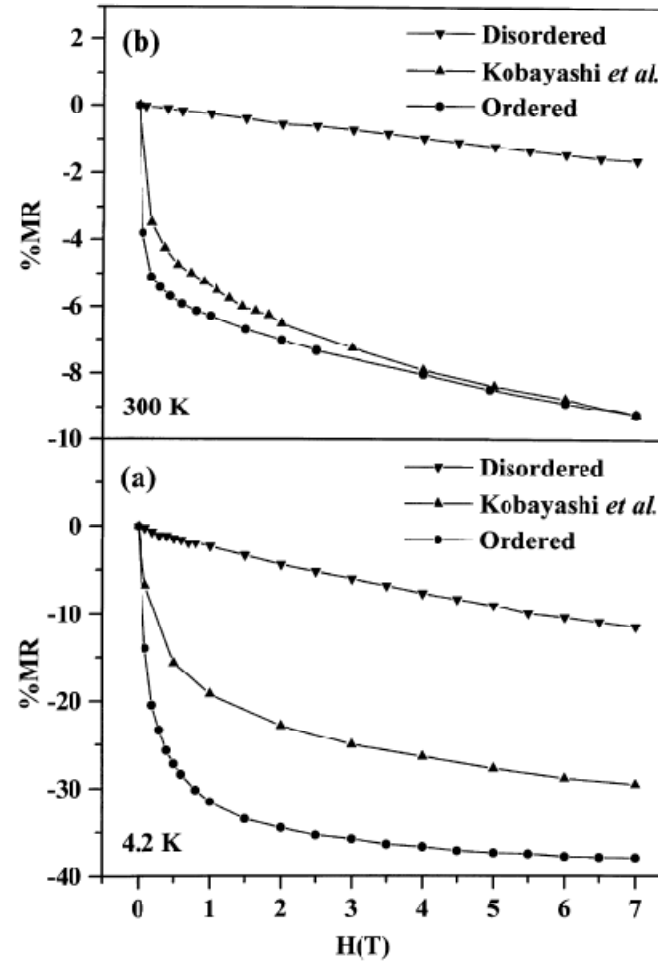


Figure 4 | Topographs (40 Å², +1.5 V) of several Mn pairs and the acceptor-level splitting energy of these pairs. **a**, Nearest-neighbour Mn acceptor pair (4 Å spacing, <110> orientation). **b**, Second-nearest-neighbour pair (5.65 Å spacing, <100> orientation). **c**, Third-nearest pair (6.92 Å spacing, <211> orientation). **d**, Sixth-nearest-neighbour pair (9.79 Å spacing, <111> orientation). Figure 3b shows the fourth-nearest-neighbour pair (8 Å spacing, <110> orientation). The fifth-nearest-neighbour is not accessible in a single (110) plane. **e**, Comparative plot of the Mn acceptor-level splitting for Mn–Mn pair interactions. Theory and experiment both show that Mn–Mn interactions are highly anisotropic, favouring <110> orientations. Error bars correspond to the standard deviation of many pairs measured on p-type GaAs (110) surfaces. ΔE, splitting energy of the acceptor levels.

Magnetoresistance in polycrystalline $\text{Sr}_2\text{FeMoO}_6$

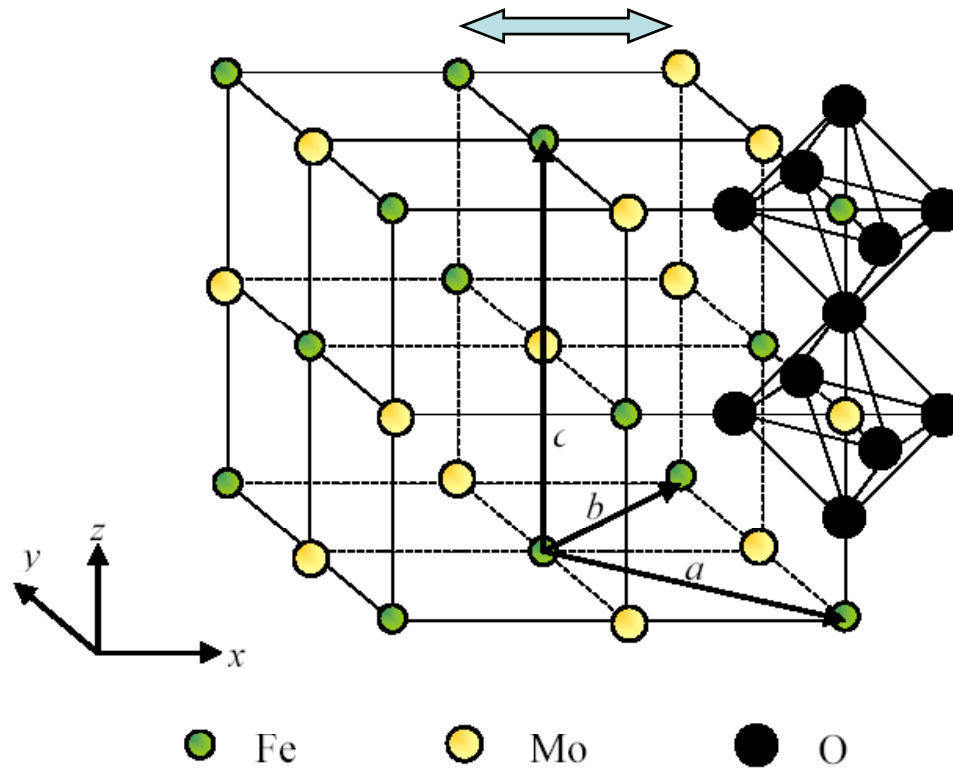


Sarma *et al.*, Solid State Comm. 114, 465 (2000).

But, why does magnetoresistance change so drastically?
Inter- or intra-grain mechanism?

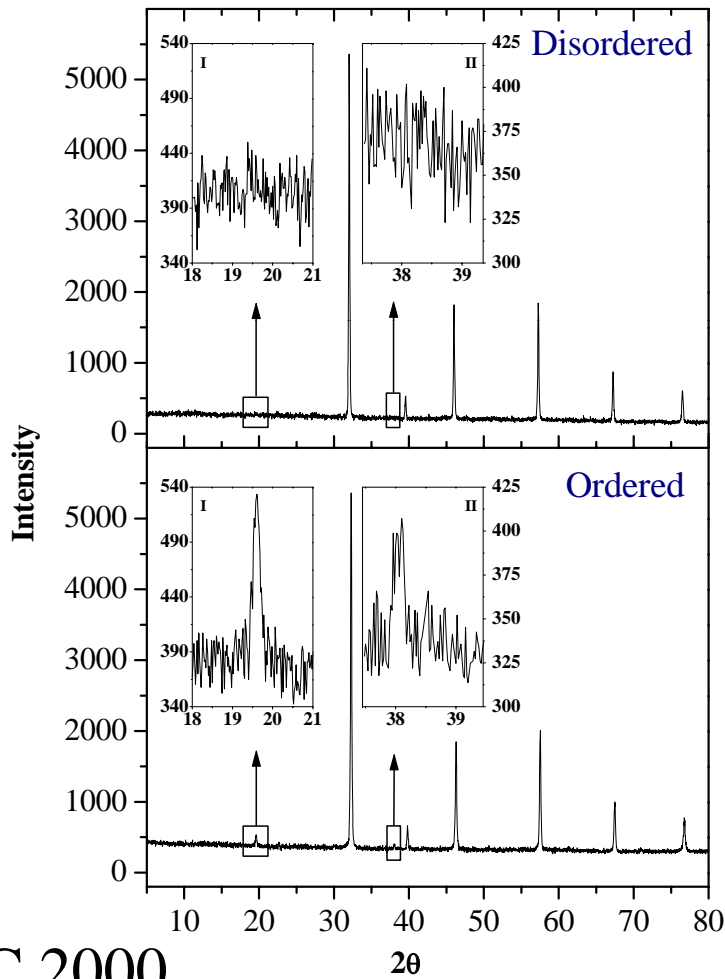
Effect of anti-site disorder in $\text{Sr}_2\text{FeMoO}_6$

What is the Fe/Mo antisite disorder?



How do we check ordering?

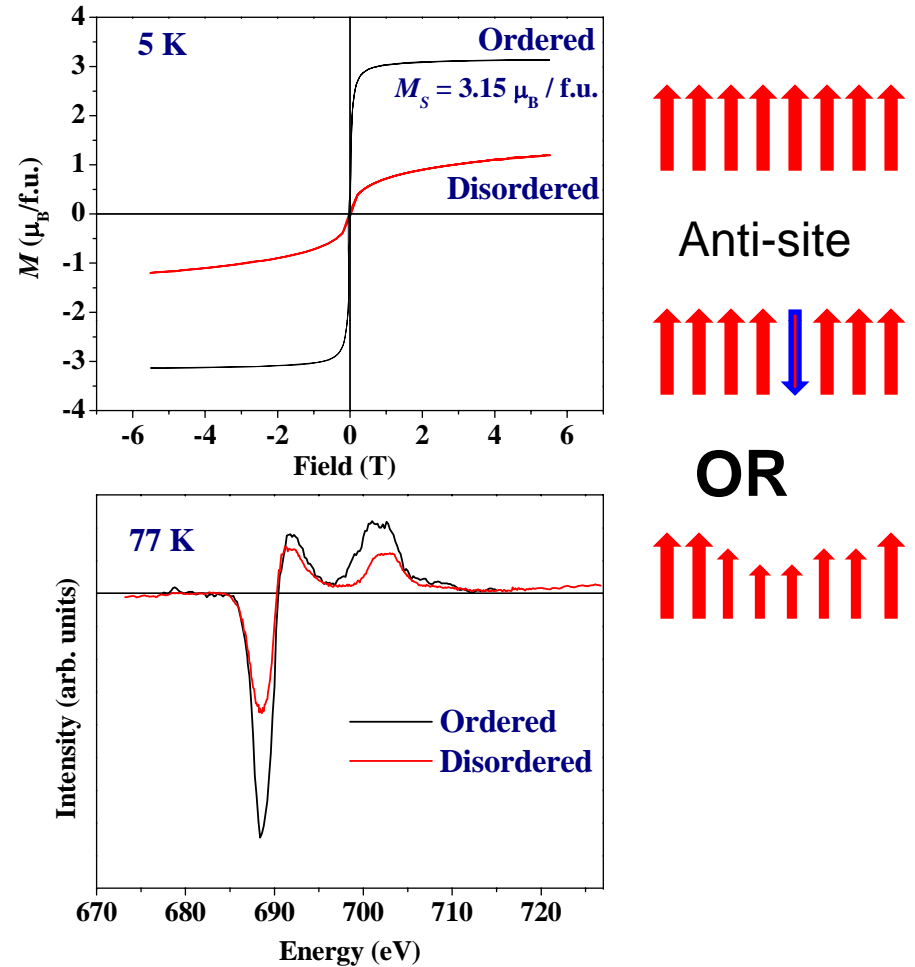
X-ray diffraction



SSC 2000

What is the effect of disorder?

Expected magnetic moment: antiparallely aligned e^{3+} ($3d^5$; $S = 5/2$) and Mo^{5+} ($4d^1$; $S = 1/2$) = $4\mu_B$ / f.u.



Why does the magnetisation change so drastically? Fe $\uparrow\downarrow$ or Mo d depolarisation?

Does anti-site give rise to antiferromagnetically coupled Fe-O-Fe pairs

OR

Is it depolarisation of Mo bands leading to decoupling of Fe's?

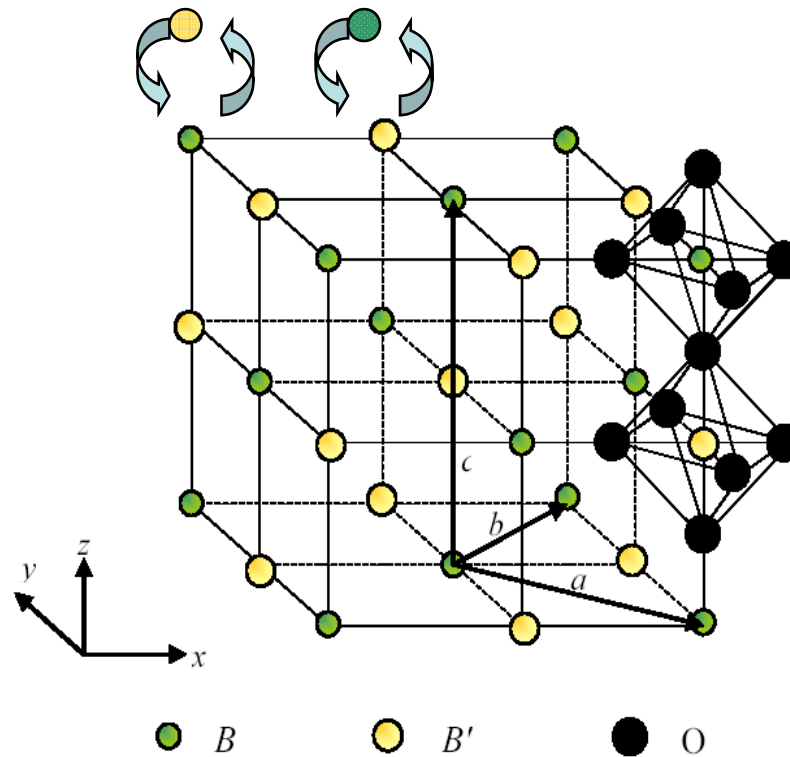


Figure 4 BL10043 18Jan2006

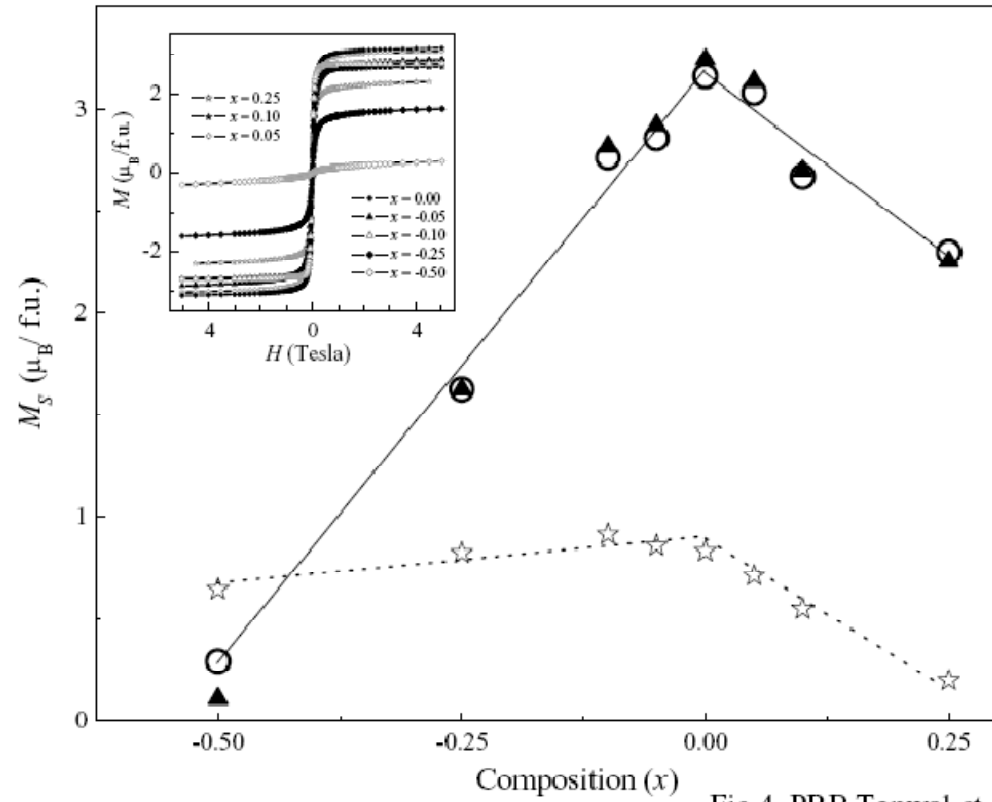
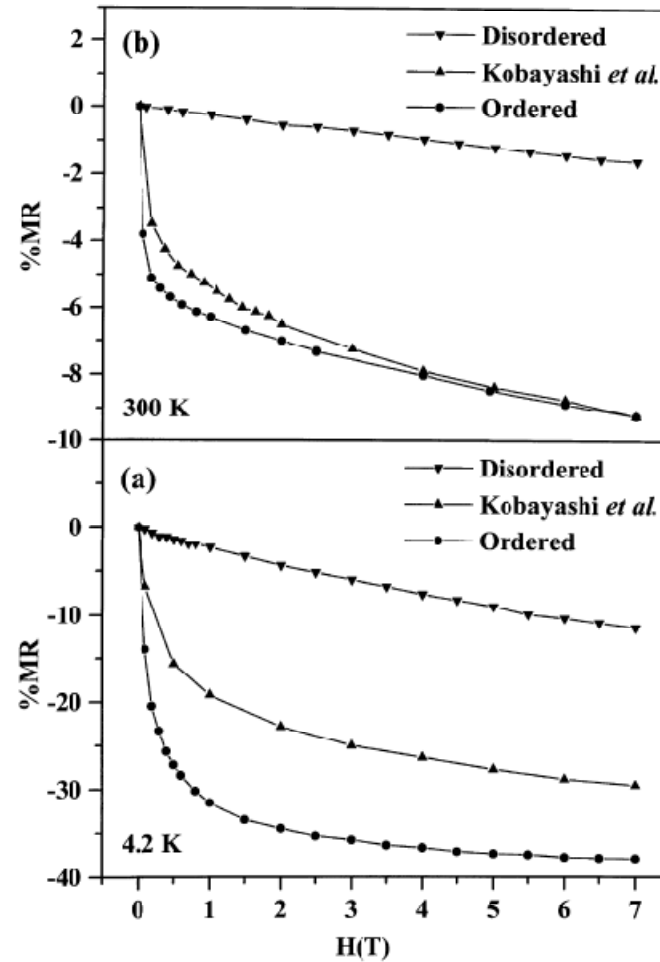


Fig 4, PRB Topwal *et al.*

**Nearest neighbour Fe-Fe pairs couple antiferromagnetically
and Mo 4d depolarisation.**

Magnetoresistance in polycrystalline $\text{Sr}_2\text{FeMoO}_6$

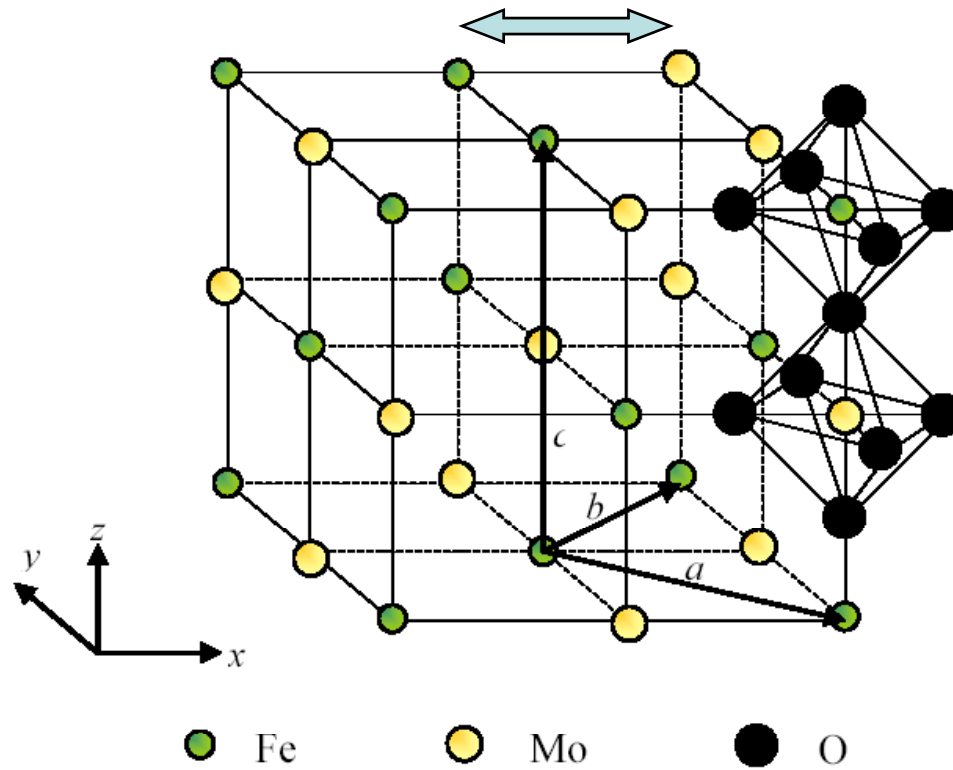


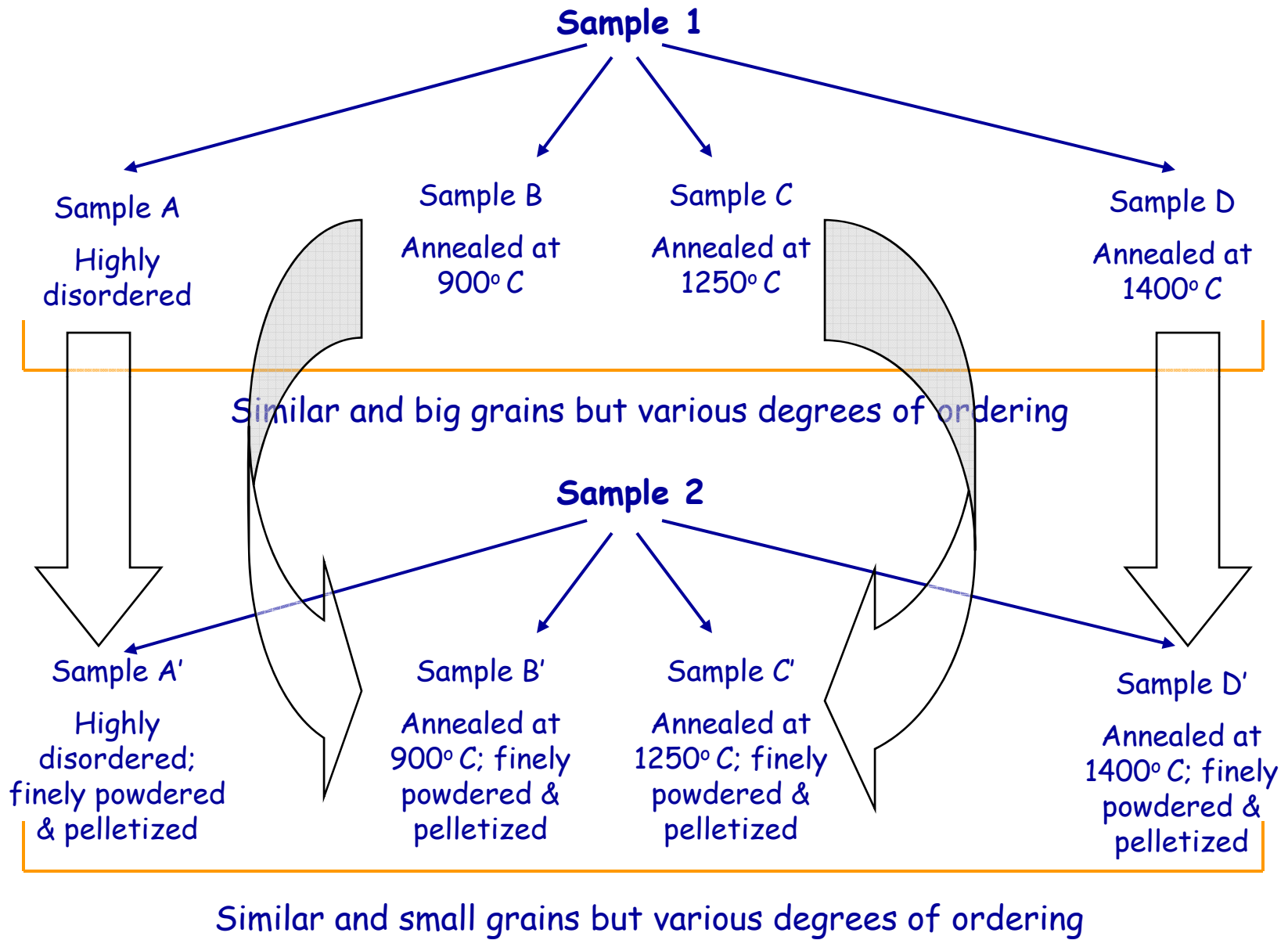
Sarma *et al.*, Solid State Comm. 114, 465 (2000).

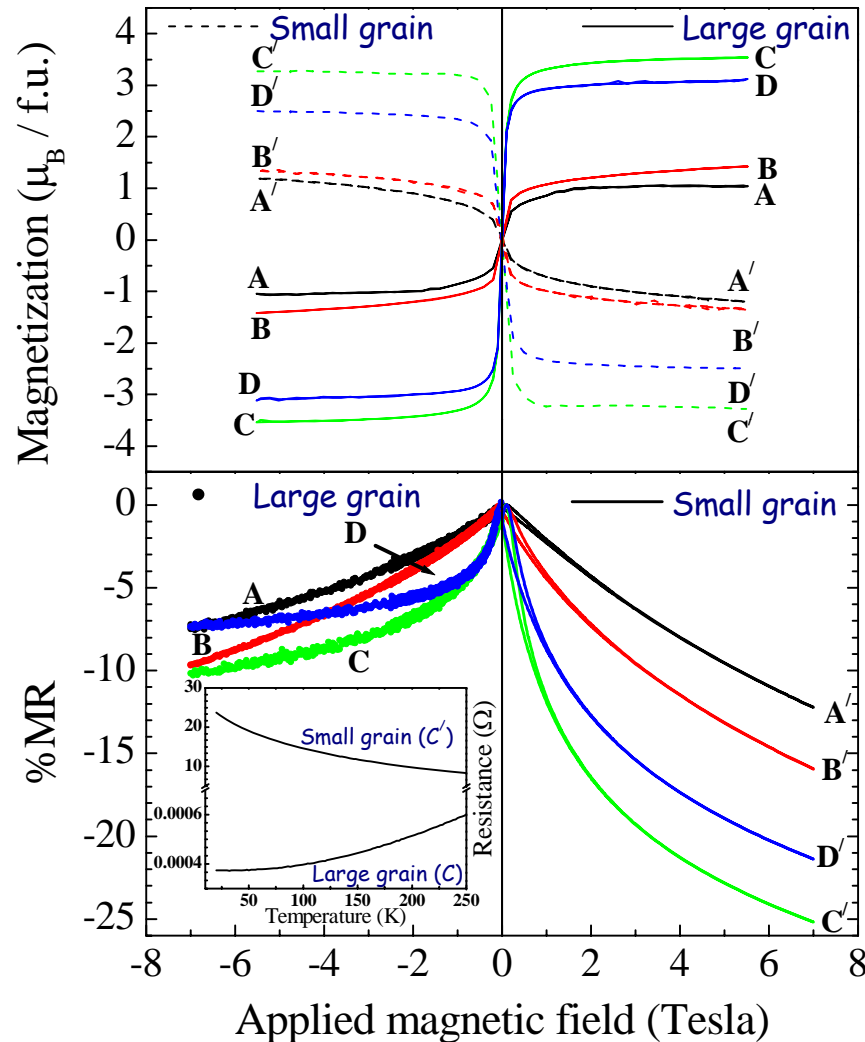
**But, why does magnetoresistance change so drastically?
Inter- or intra-grain mechanism?**

Effect of anti-site disorder in $\text{Sr}_2\text{FeMoO}_6$

What is the Fe/Mo antisite disorder?







- Small grain samples have much larger %MR compared to the large grain ones → **Inter-grain mechanism.**
- Within the small grain samples, samples with higher ordering and therefore, lower anti-site defects show larger %MR → **Effect of anti-site (intra-grain) boundaries, if any, is dominated over by other (inter-grain and magnetisation) effects.**
- **Inter-grain tunnelling MR should have some tell-tale signatures, such as %MR $\sim M^2$ and consistent hysteresis.**

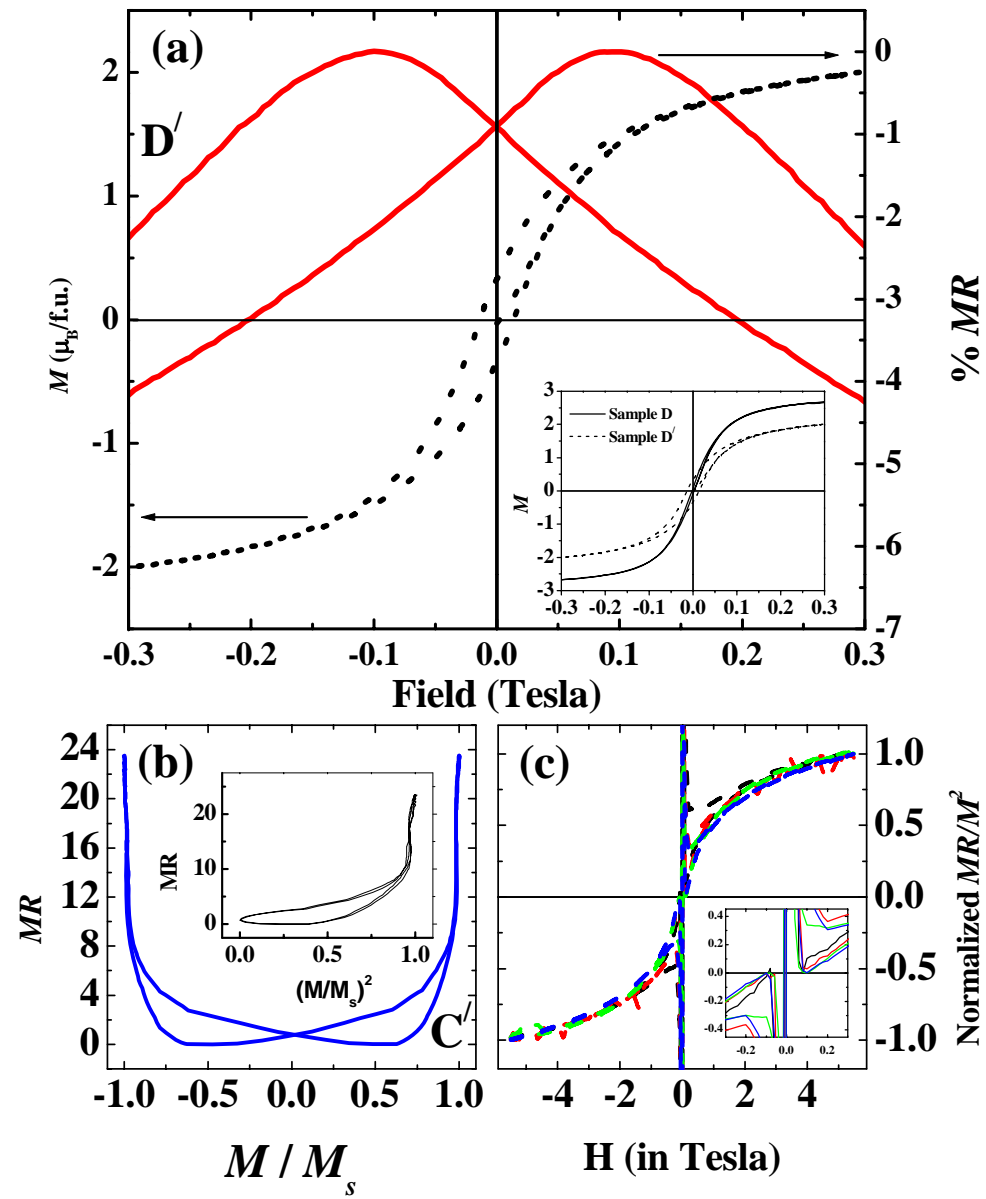
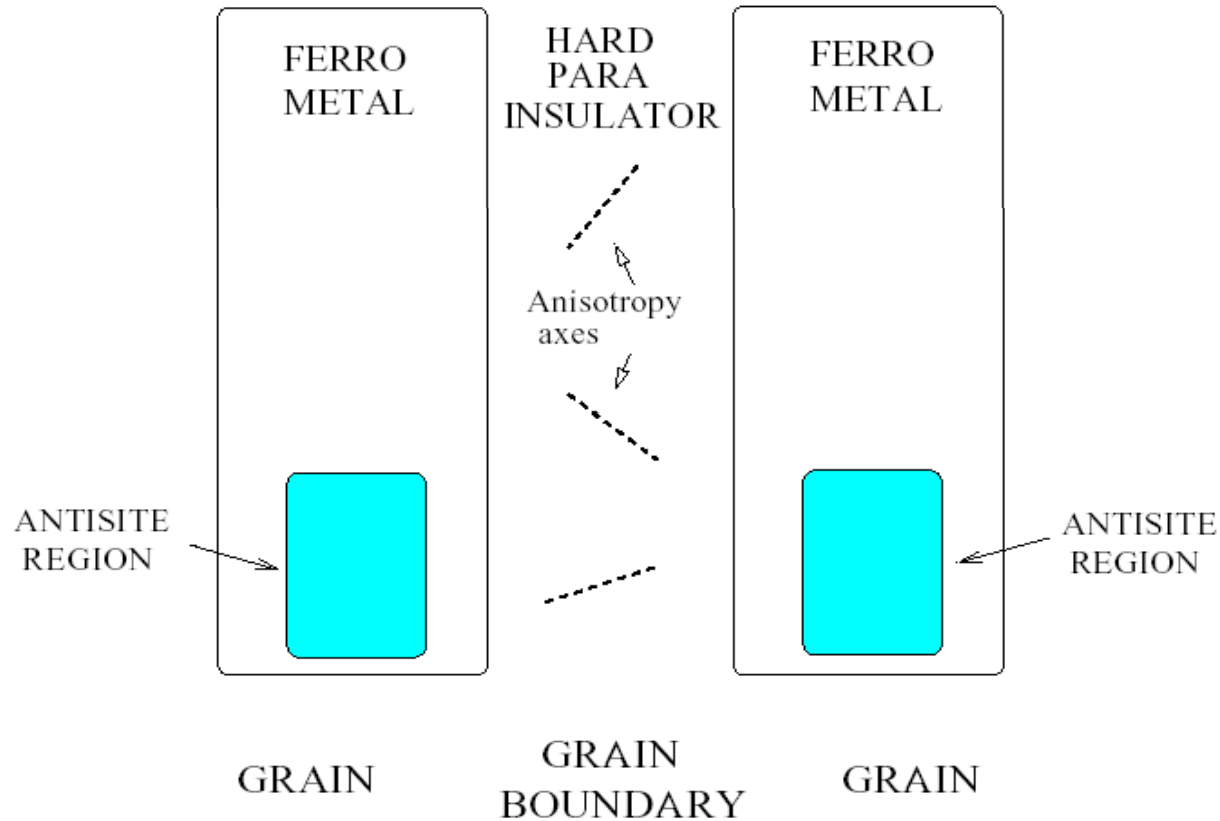


Fig. 2
Sarma *et al.*

TRILAYER MAGNETIC TUNNEL JUNCTION



- Unlike standard TMR calculations, we consider the intermediate insulating region to have magnetic properties also.
- The insulating region, in addition to being paramagnetic, is assumed to have magnetic anisotropy, with randomly oriented anisotropy axes.

Calculated results for MR

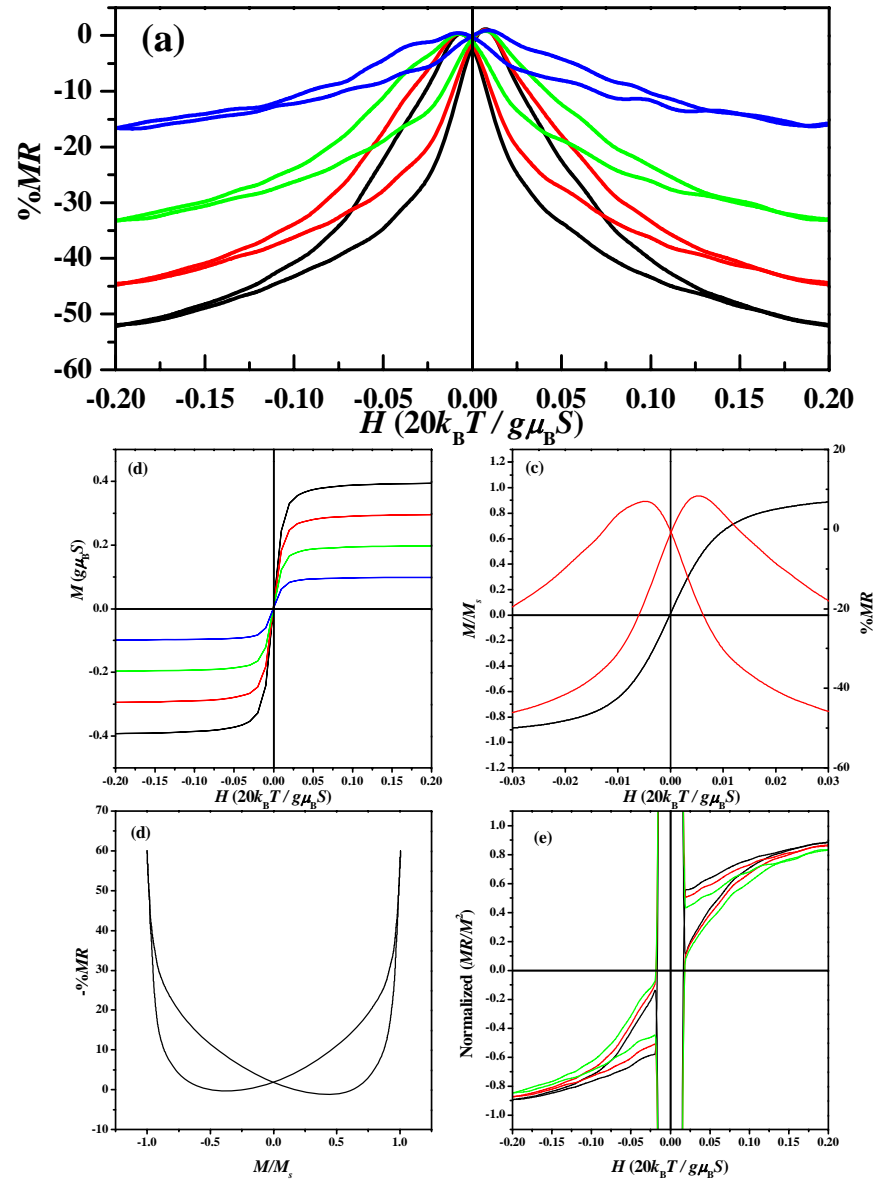


Fig. 3

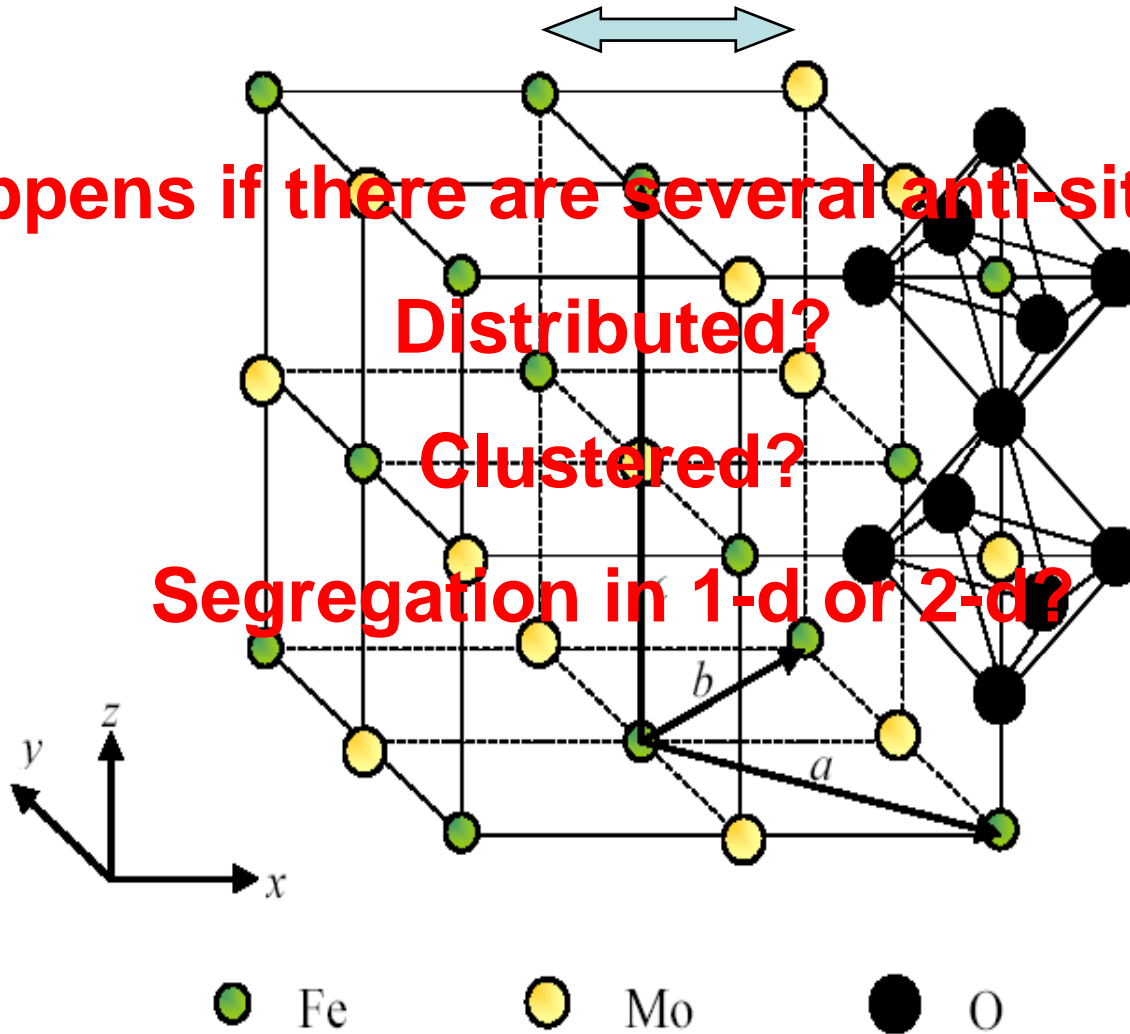
Effect of anti-site disorder in $\text{Sr}_2\text{FeMoO}_6$

What happens if there are several anti-site defects?

Distributed?

Clustered?

Segregation in 1-d or 2-d?



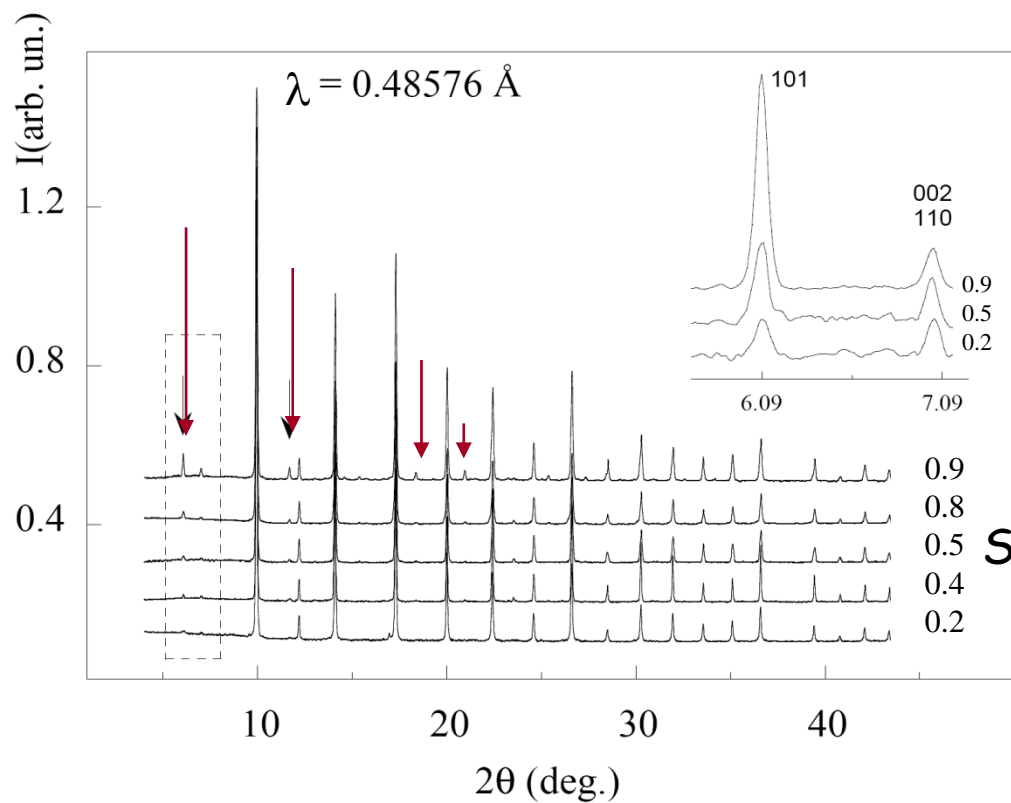
Experimental:

GILDA-BM08 @ ESRF

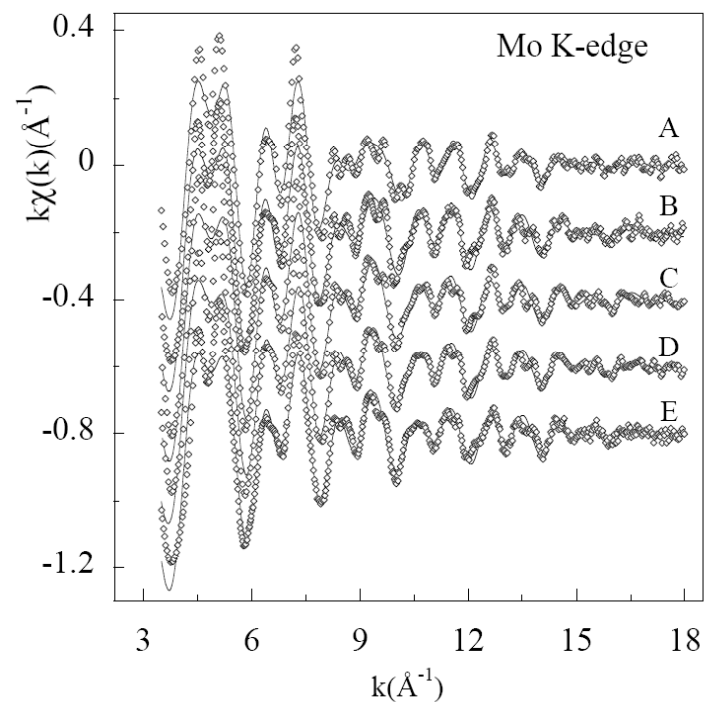
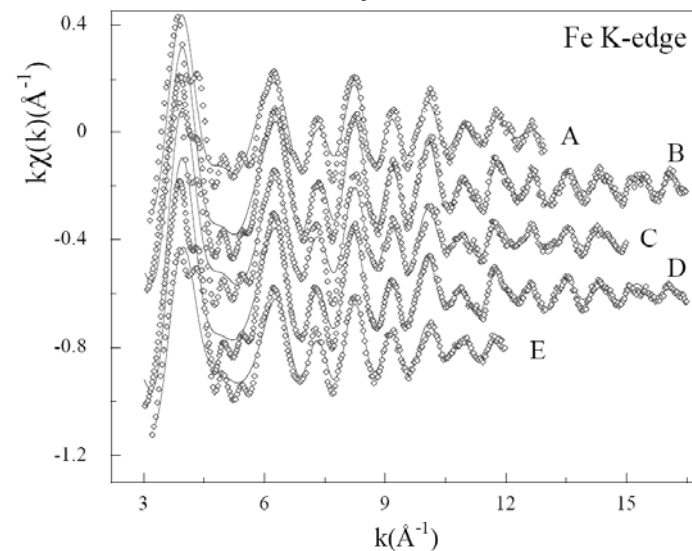
SR-XRD and XAFS

(Fe & Mo K edges) on $\text{Sr}_2\text{FeMoO}_6$
with different cation disorder (S)

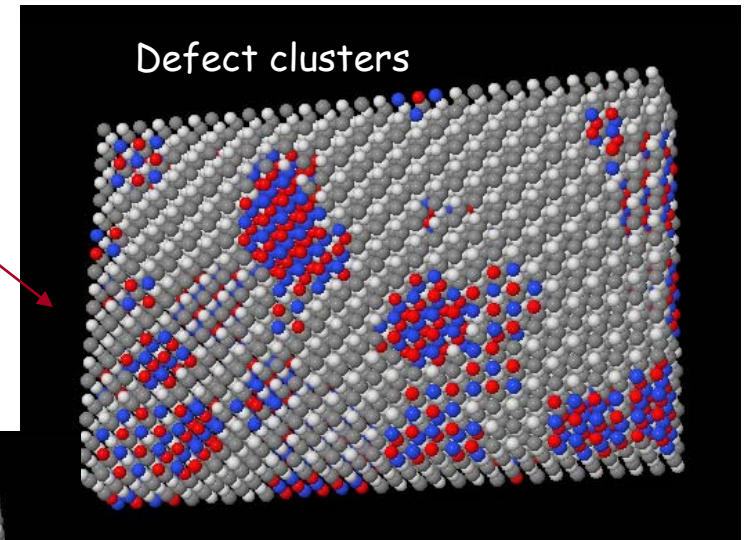
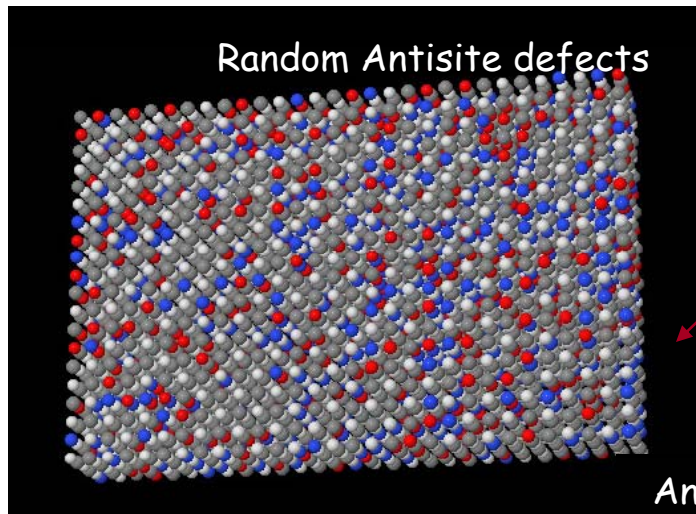
XRD



XAFS

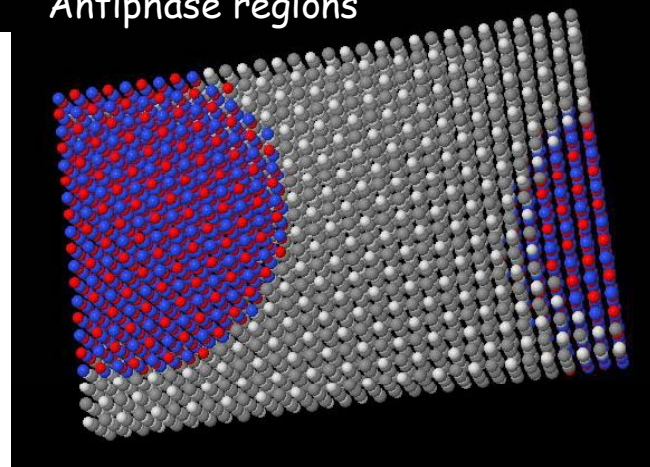


The disorder from a local perspective



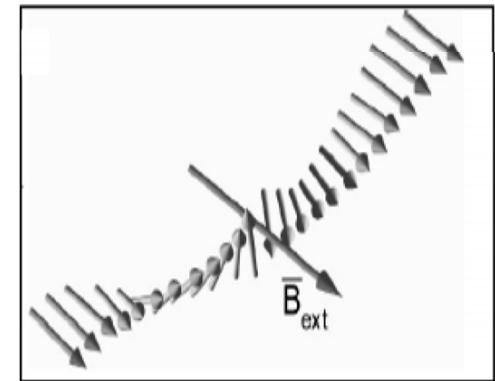
$$S = 0.51$$

Antiphase regions



$$S = 2x - 1$$

S takes into account only for the number of defects (Fe_B or Mo_A), not their arrangement



The nature of defects must affect the magnetic and magnetotransport response of the system

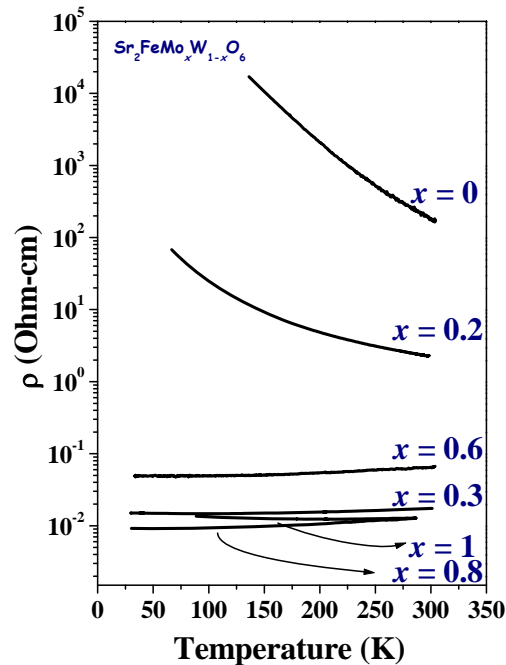
$\text{Sr}_2\text{FeMo}_x\text{W}_{1-x}\text{O}_6$

$\text{Sr}_2\text{FeMoO}_6$: Half metallic ferromagnetic metal ($T_C \sim 420$ K)

Nominally Fe^{3+} and Mo^{5+} .

Sr_2FeWO_6 : Antiferromagnetic insulator ($T_N \sim 37$ K); Nominally Fe^{2+} localized moments are coupled *via* superexchange through nonmagnetic O^{2-} and W^{6+} sites.

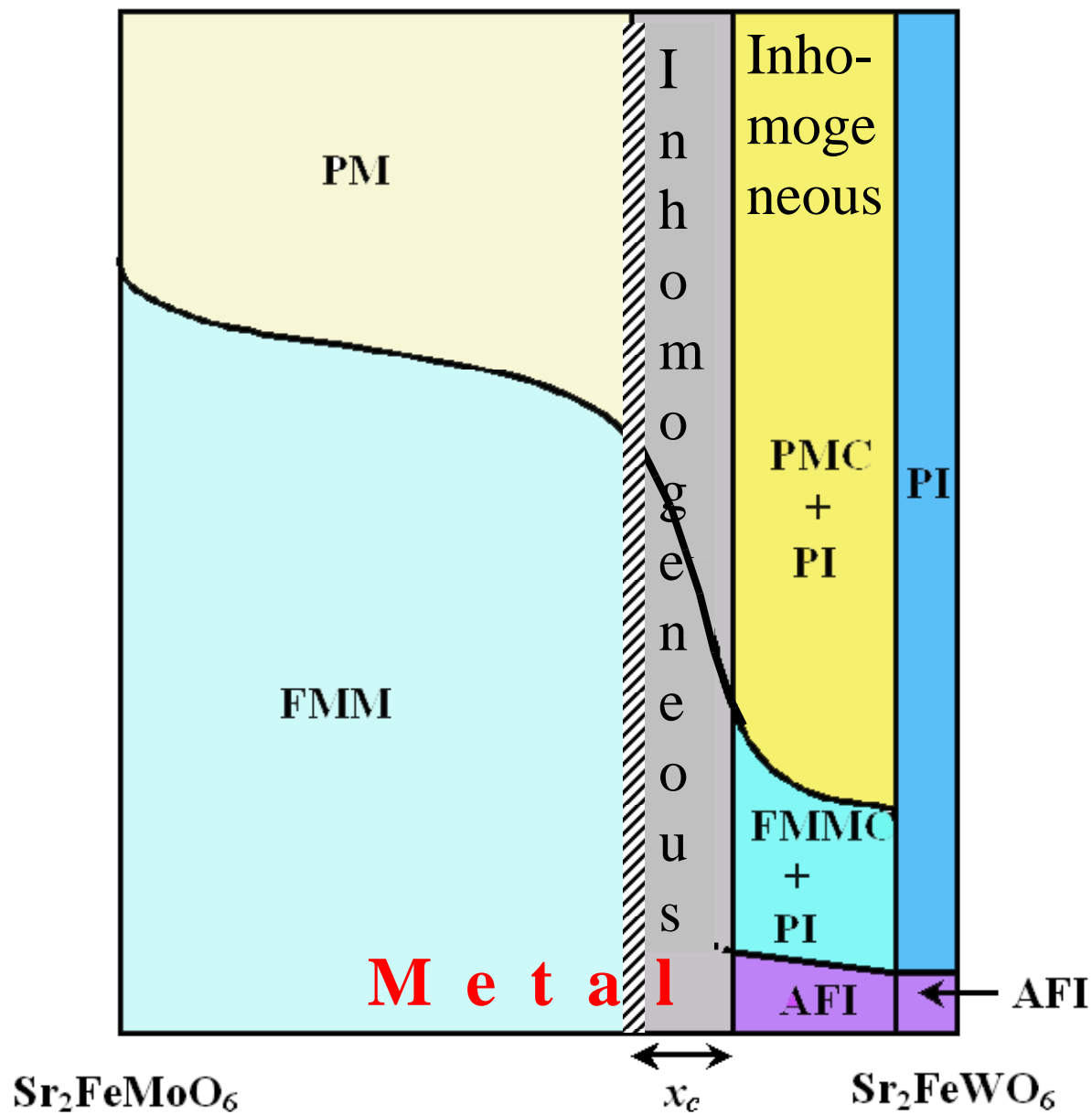
Therefore, $\text{Sr}_2\text{FeMo}_x\text{W}_{1-x}\text{O}_6$ assures magnetic and metal-insulator transition over the composition range.



What drives this MIT?

S. Ray et al., J. Physics: Condensed Matter
13, 607 (2001).

T-x Phase diagram of $\text{Sr}_2\text{FeMo}_x\text{W}_{1-x}\text{O}_6$



Ray et al., unpublished

Applications of XAFS: Manganites

Temperature dependence of non-Debye disorder in doped manganites

C. Meneghini, R. Cimino, S. Pascarelli, S. Mobilio, C. Raghunathan and D. D. Sarma

PHYSICAL REVIEW B VOLUME 56, 3520, 1997

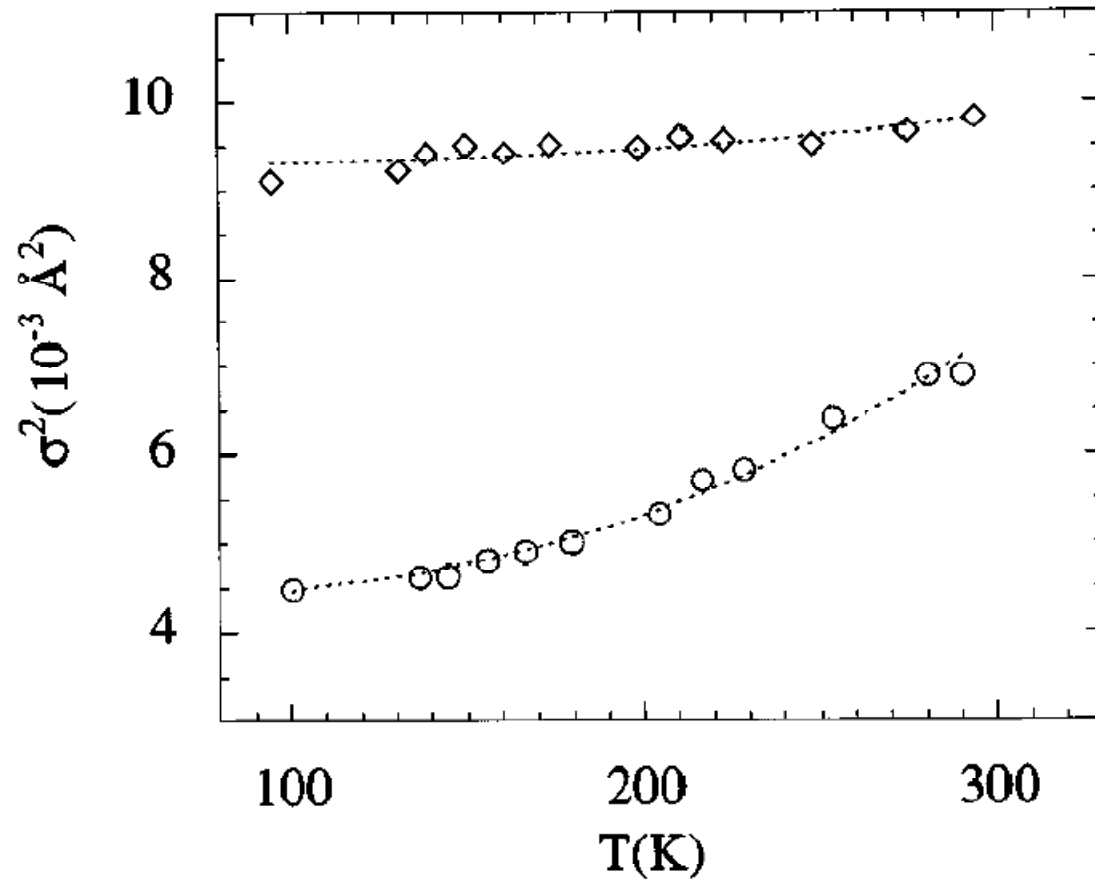


FIG. 1. Debye-Waller factor from EXAFS analysis for LaMnO_3 (diamonds) and MnO (circles) samples. The dashed lines are the best fit data obtained using a correlated Debye model (see text).

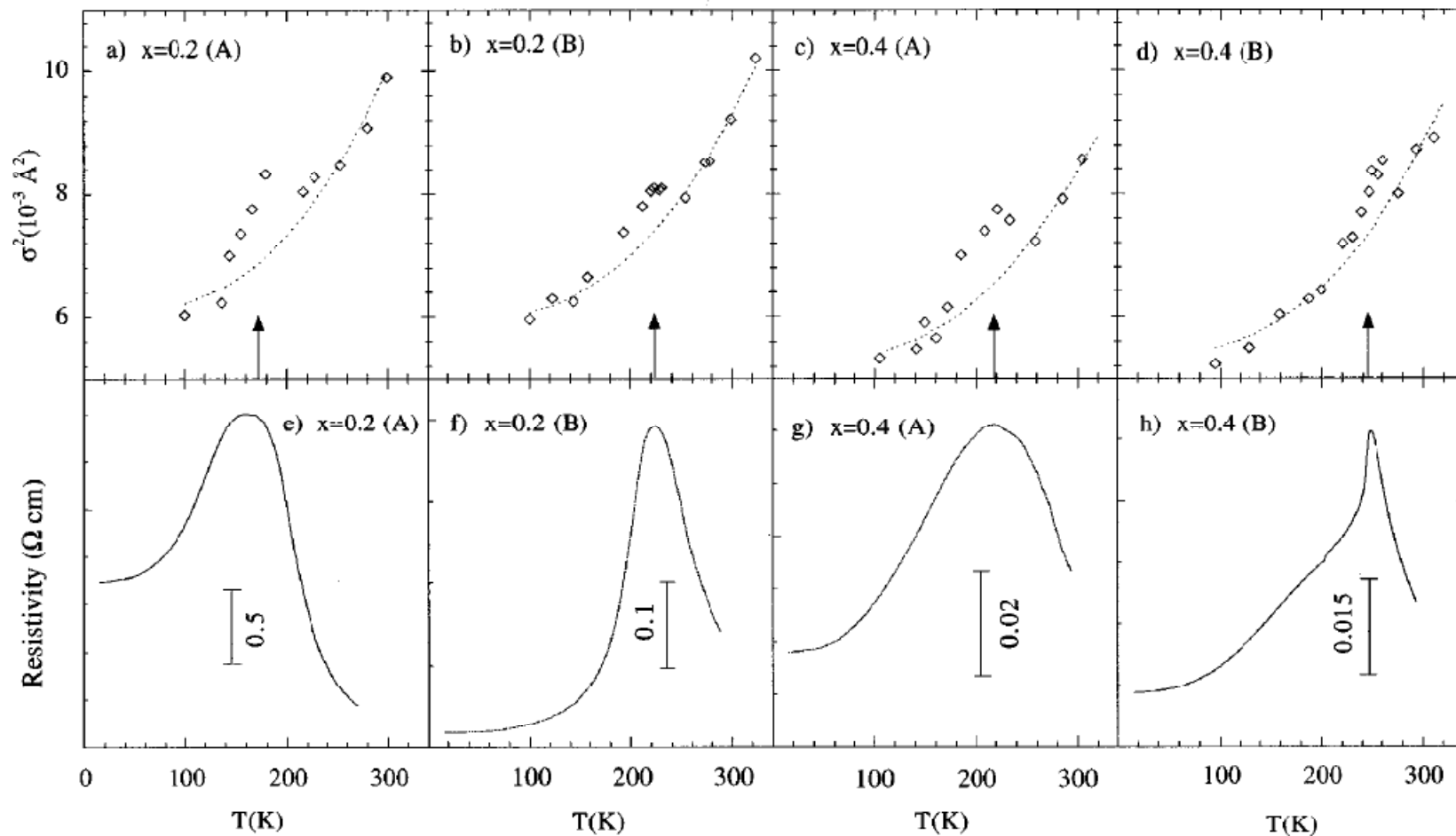


FIG. 2. Top panels (a)–(d): Debye-Waller disorder factor (diamonds) for Ca-doped $\text{La}_{1-x}\text{MnO}_3\text{Ca}_x$ manganites. The arrows indicate the metal-insulator transition temperature and the dashed lines are the Debye-like contribution to the total disorder factor (see text). Bottom panels (e)–(h): resistivity data.

Local structure of hole-doped manganites: influence of temperature and applied magnetic field.

C. Meneghini, C Castellano, S Mobili , Ashwani Kumar, S Ray and D D Sarma

J. Phys.: Condens. Matter **14 (2002) 1967–1974**

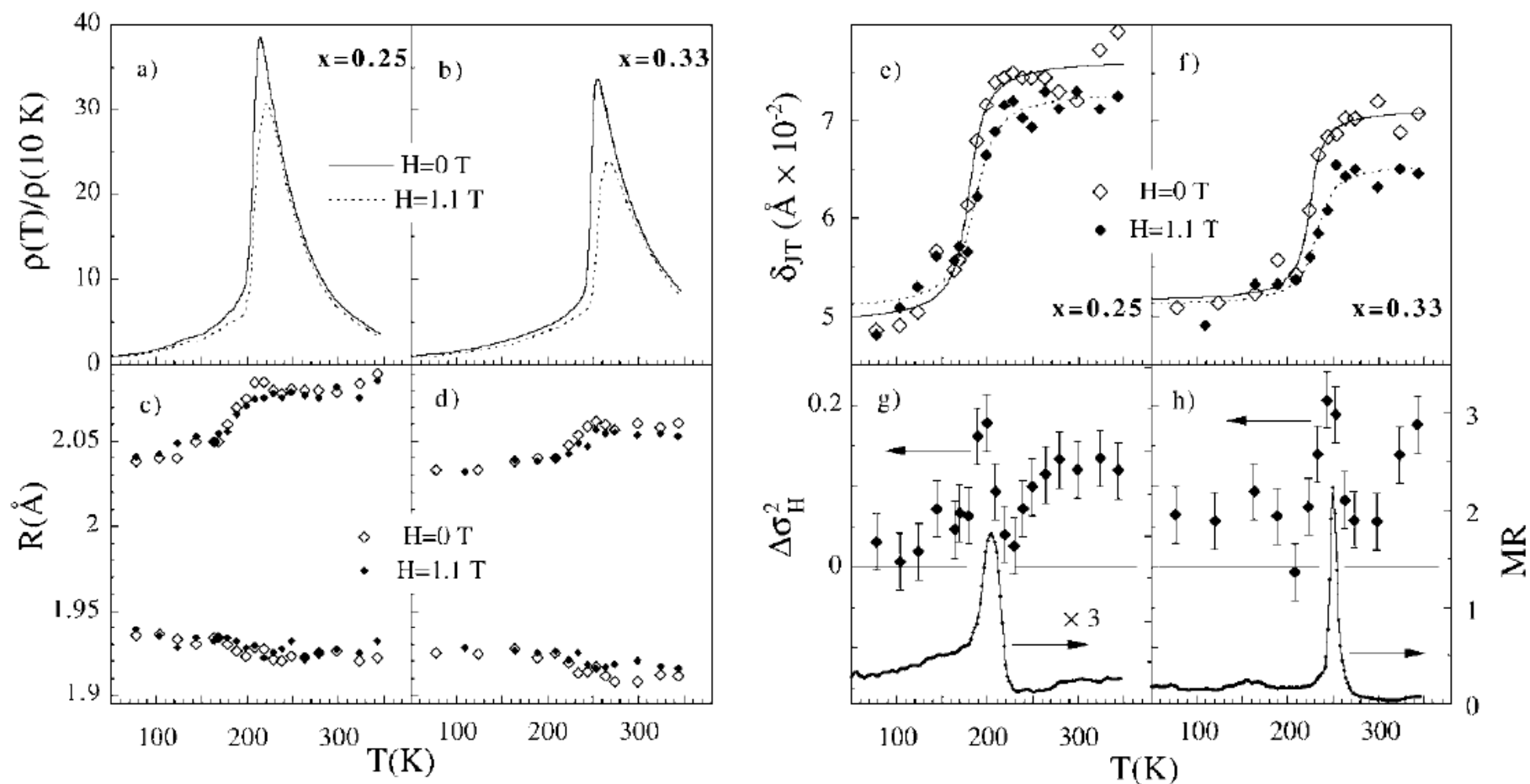


Figure 3. (a), (b) Resistivity, (c), (d) bimodal distribution of Mn–O bond lengths and (e), (f) local Jahn–Teller distortions of the MnO₆ octahedron in the absence ($H = 0$ T) and presence ($H = 1.1$ T) of magnetic field as a function of temperature. In panels (g) and (h), the relative variations in the DW factors ($\Delta\sigma_H^2 = (\sigma_H^2 - \sigma_0^2)/\sigma_H^2$) and magnetoresistance ($MR = (R_H - R_0)/R_H$) as a function of temperature are shown. Panels (a), (c), (e) and (g) ((b), (d), (f) and (h)) refer to the $x = 0.25$ (0.33) sample.

Thank you for your attention